



N - CHANNEL ENHANCEMENT MODE POWER MOSFET

TF060N03N

● General Description

The TF060N03N uses advanced trench technology and design to provide excellent RDS(ON) withlowgate charge. It can be used in a wide variety of applications.

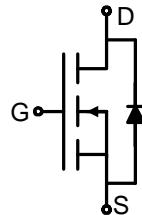
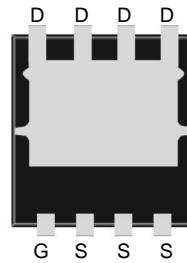
● Features

- Advance device constructure
- Low $R_{DS(ON)}$ to minimize conduction loss
- Low Gate Charge for fast switching
- Low Thermal resistance

● Application

Synchronous Rectification for AC-DC/DC-DC converter
Power Tools

● Product Summary

 $V_{DS}=30V \quad I_D=65A$ $R_{DS(ON)(4.5V\ typ)}=5.5m\Omega$ $R_{DS(ON)(2.5V\ typ)}=9.8m\Omega$ 

PDFNWB5x6-8L

● Package Marking and Ordering Information:

Part NO.	TF060N03N
Marking1	060N03N
Marking2	TF:tuofeng; Y:year code; XX:Week; AA:device code;
Basic ordering unit (pcs)	5000

● Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D@T_C=25^\circ C$	65	A
	$I_D@T_C=75^\circ C$	45	A
	$I_D@T_C=100^\circ C$	40	A
Pulsed Drain Current ①	I_{DM}	180	A
Total Power Dissipation	$P_D@T_C=25^\circ C$	45	W
Total Power Dissipation	$P_D@T_A=25^\circ C$	2.0	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	105	mJ



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• Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	-	5.5	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	60	° C/W
Soldering temperature, wavesoldering for 8 s	T _{sold}	-	-	265	° C

• Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	30	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA	1.1	1.5	2.1	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =30 V _{GS} = 0V	-	-	1.0	μA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V , V _{DS} = 0V	-	-	±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	5.5	7.0	mΩ
		V _{GS} =4.5V, I _D =20A	-	9.8	11	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 25V, I _D =20A	-	20	-	S
Source-drain voltage	V _{SD}	I _S =20A	-	0.84	1.20	V

• Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz V _{DS} =15V V _{GS} = 0V	-	1400	-	pF
Output capacitance	C _{oss}		-	205	-	
Reverse transfer capacitance	C _{rss}		-	177	-	

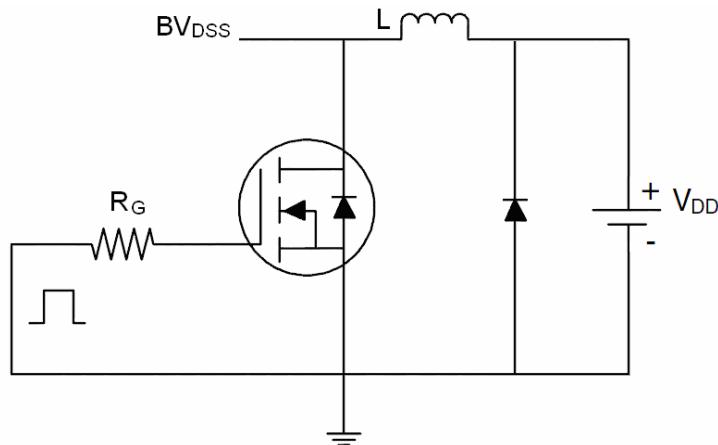
• Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} = 15V I _D = 20A V _{GS} = 10V	-	32.3	-	nC
Gate - Source charge	Q _{gs}		-	4.9	-	
Gate - Drain charge	Q _{gd}		-	6.9	-	

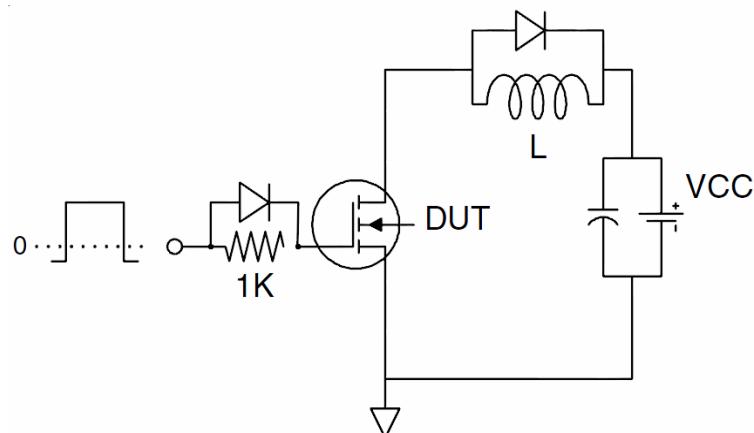
Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Test Circuit

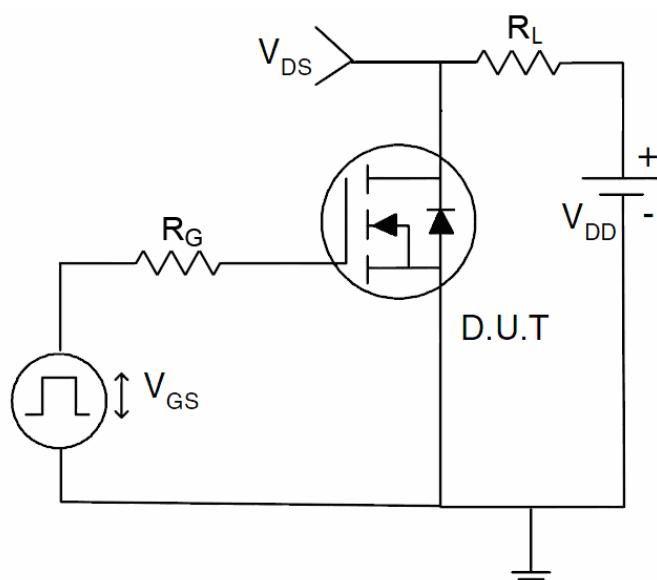
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

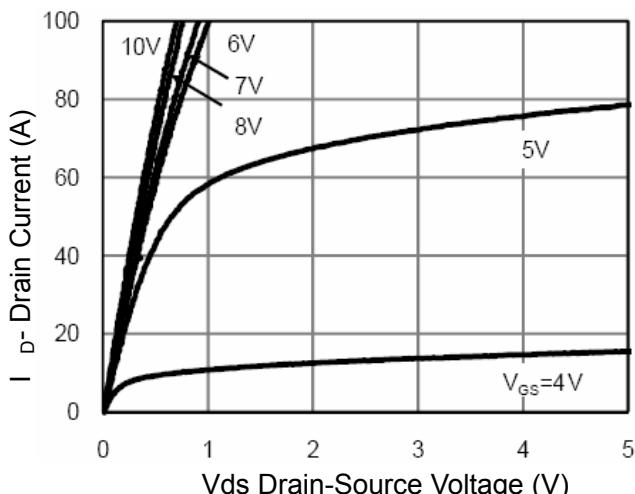


Figure 1 Output Characteristics

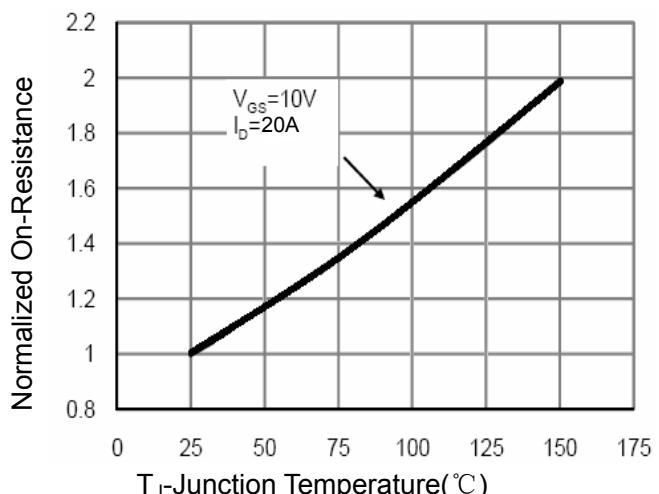


Figure 4 R_{DSON} -Junction Temperature

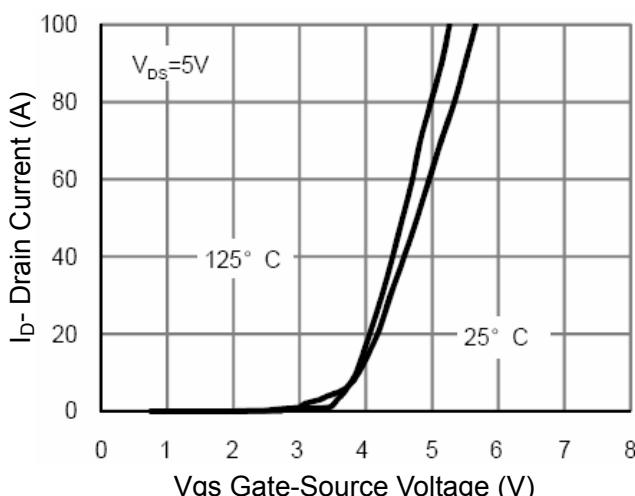


Figure 2 Transfer Characteristics

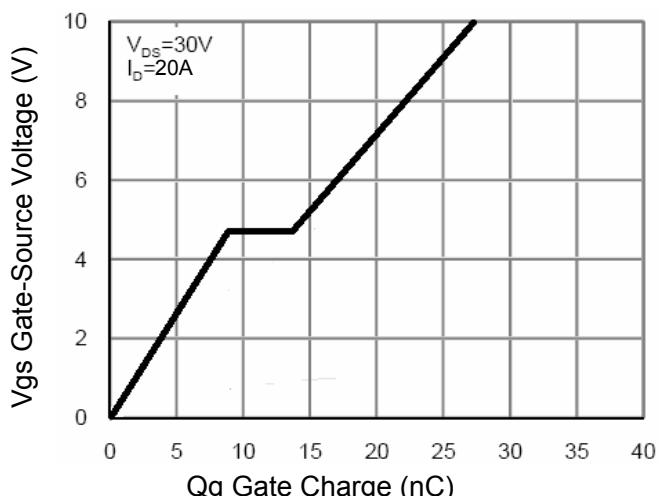


Figure 5 Gate Charge

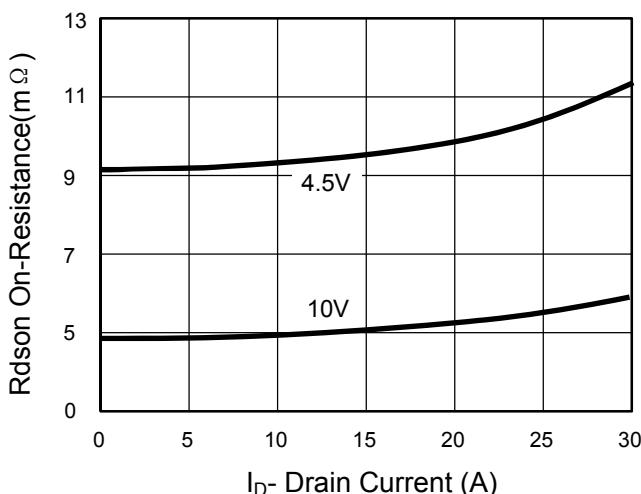


Figure 3 R_{DSON} - Drain Current

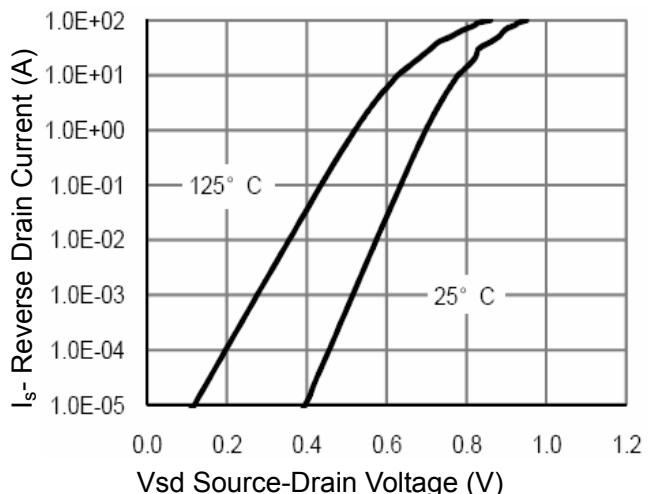


Figure 6 Source-Drain Diode Forward

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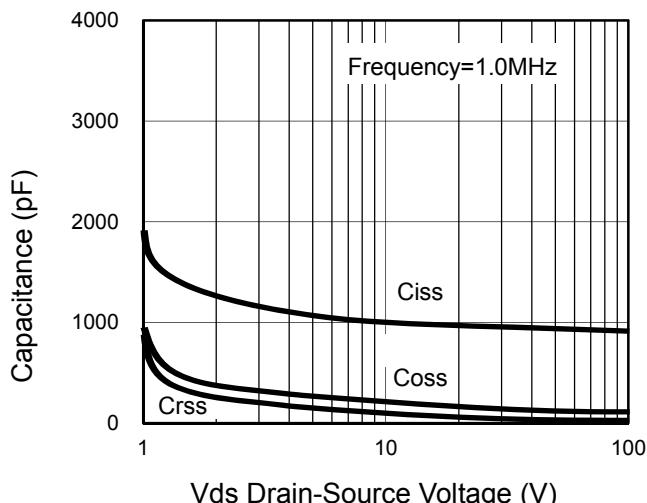


Figure 7 Capacitance vs Vds

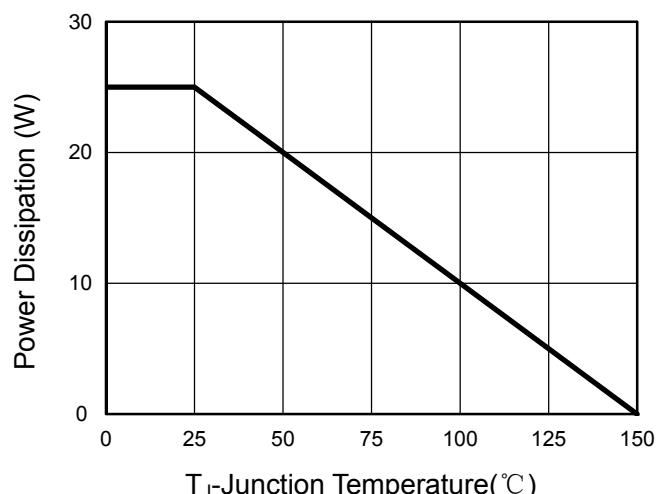


Figure 9 Power De-rating

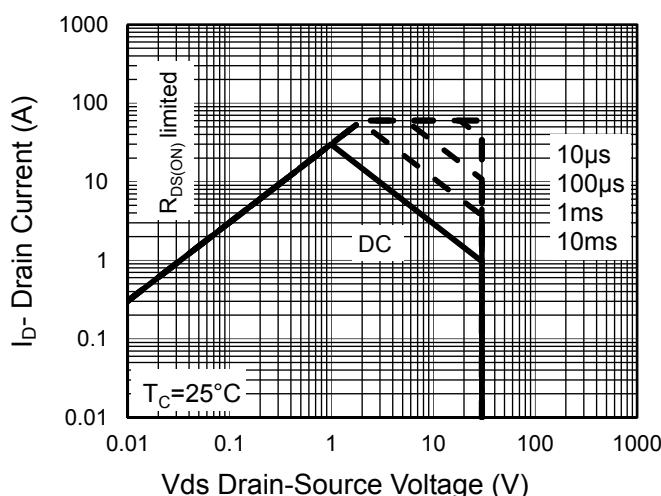


Figure 8 Safe Operation Area

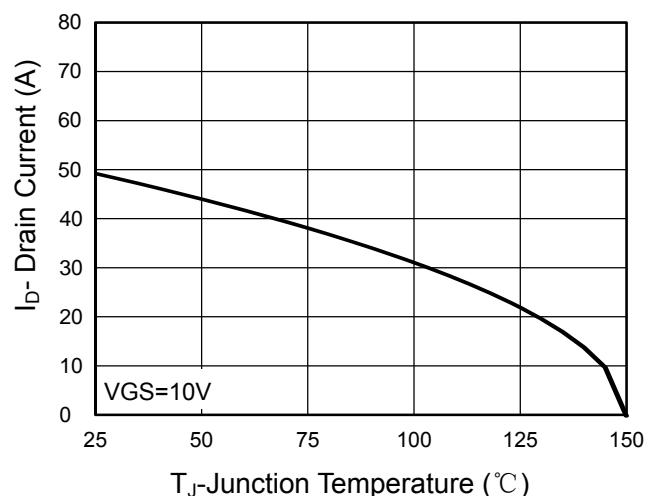


Figure 10 Current De-rating

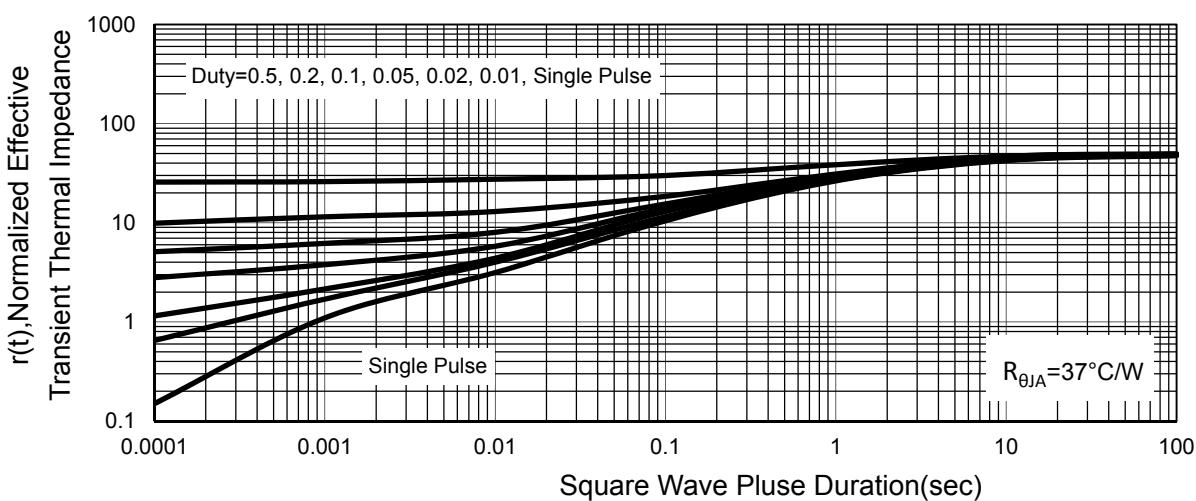


Figure 11 Normalized Maximum Transient Thermal Impedance

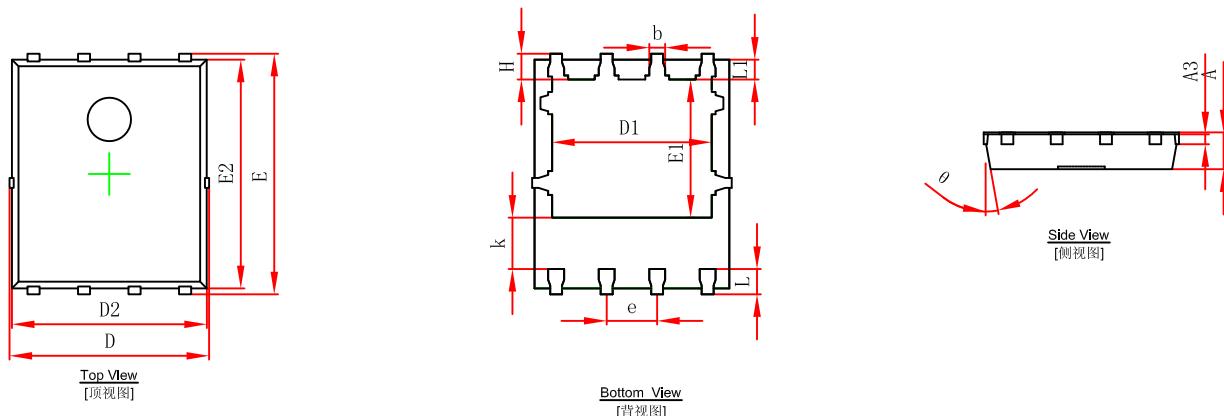


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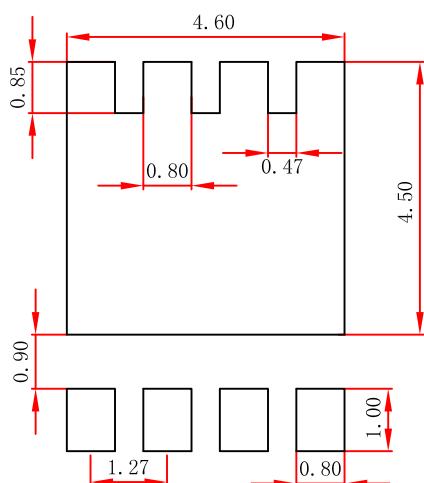
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PDFNWB5x6-8L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

PDFNWB5x6-8L Suggested Pad Layout



Note:

1. Controlling dimension:in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.